

International
IR Rectifier

SMPS MOSFET

PD - 94492
IRLR7811W

HEXFET[®] Power MOSFET

Applications

- High Frequency Synchronous Buck Converters for Computer Processor Power
- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use

V_{DSS}	R_{DS(on)} max	Q_g
30V	10.5mΩ	19nC

Benefits

- Very Low RDS(on) at 4.5V V_{GS}
- Ultra-Low Gate Impedance
- Fully Characterized Avalanche Voltage and Current



Absolute Maximum Ratings

	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	64④	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	45④	
I _{DM}	Pulsed Drain Current ①	260	
P _D @ T _C = 25°C	Power Dissipation	71	W
P _D @ T _A = 100°C	Power Dissipation*	1.5	
	Linear Derating Factor	0.48	W/°C
V _{GS}	Gate-to-Source Voltage	±12	V
T _J	Operating Junction and	-55 to + 175	°C
T _{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case	—	2.1	°C/W
R _{θJA}	Junction-to-Ambient (PCB mount)*	—	50	
R _{θJA}	Junction-to-Ambient	—	110	

Notes ① through ④ are on page 9

www.irf.com



IRLR7811W

International
IR Rectifier

Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	30	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	27	—	mV/°C	Reference to 25°C, I _D = 1mA ⑥
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	6.5	10	mΩ	V _{GS} = 10V, I _D = 15A ④
		—	7.5	12		V _{GS} = 4.5V, I _D = 12A
V _{GS(th)}	Gate Threshold Voltage	—	1.5	2.5	V	V _{DS} = V _{GS} , I _D = 250μA
ΔV _{GS(th)} /ΔT _J	Gate Threshold Voltage Coefficient	—	-5.0	—	mV/°C	
I _{DSS}	Drain-to-Source Leakage Current	—	—	30	μA	V _{DS} = 24V, V _{GS} = 0V
		—	—	150		V _{DS} = 24V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 12V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -12V
g _{fs}	Forward Transconductance	58	—	—	S	V _{DS} = 15V, I _D = 12A
Q _g	Total Gate Charge Control Fet	—	21	31	nC	
Q _{gs1}	Pre-V _{th} Gate-Source Charge	—	5.0	—		
Q _{gs2}	Post-V _{th} Gate-Source Charge	—	1.7	—		
Q _{gd}	Gate-to-Drain Charge	—	6.6	—		
Q _{godr}	Gate Charge Overdrive	—	5.5	—		
Q _{sw}	Switch Charge (Q _{gs2} + Q _{gd})	—	8.3	—		
Q _g	Total Gate Charge Sync Fet	—	17	—		
Q _{oss}	Output Charge	—	10	—		V _{DS} = 16V, V _{GS} = 0V
R _g	Gate Resistance	—	1.6	—		
t _{d(on)}	Turn-On Delay Time	—	18	—	ns	V _{DD} = 16V, V _{GS} = 4.5V ④ I _D = 12A Clamped Inductive Load
t _r	Rise Time	—	4.8	—		
t _{d(off)}	Turn-Off Delay Time	—	11	—		
t _f	Fall Time	—	23	—		
C _{iss}	Input Capacitance	—	2260	—	pF	V _{GS} = 0V V _{DS} = 15V f = 1.0MHz
C _{oss}	Output Capacitance	—	420	—		
C _{rss}	Reverse Transfer Capacitance	—	180	—		

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E _{AS}	Single Pulse Avalanche Energy②	—	140	mJ
I _{AR}	Avalanche Current①	—	12	A
E _{AR}	Repetitive Avalanche Energy①	—	7.1	mJ

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	64④	A	MOSFET symbol showing the integral reverse p-n junction diode.
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	260		
V _{SD}	Diode Forward Voltage	—	—	1.2	V	T _J = 25°C, I _S = 12A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	30	45	ns	T _J = 25°C, I _F = 12A
Q _{rr}	Reverse Recovery Charge	—	27	41	nC	di/dt = 100A/μs ④
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

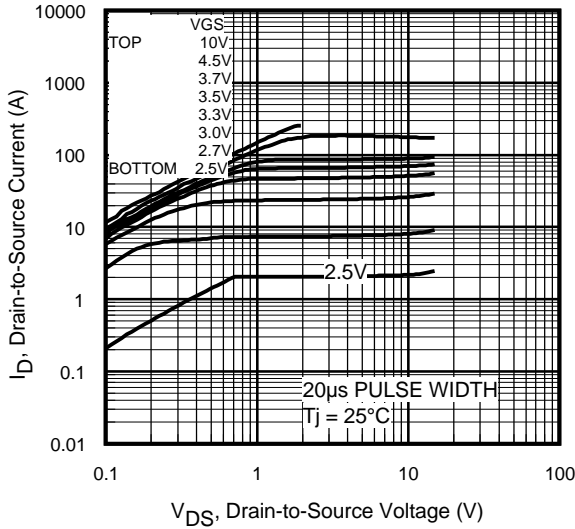


Fig 1. Typical Output Characteristics

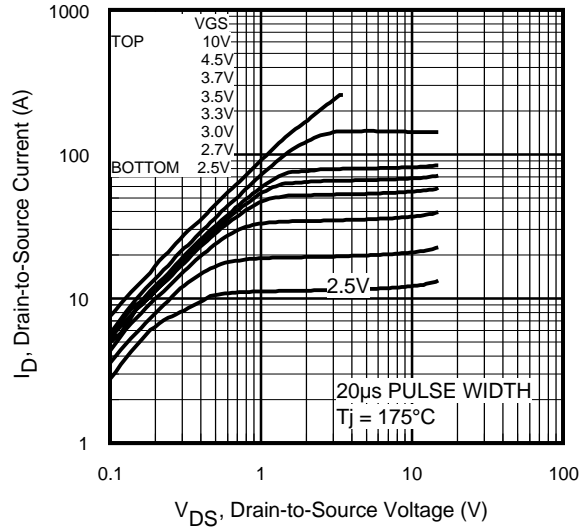


Fig 2. Typical Output Characteristics

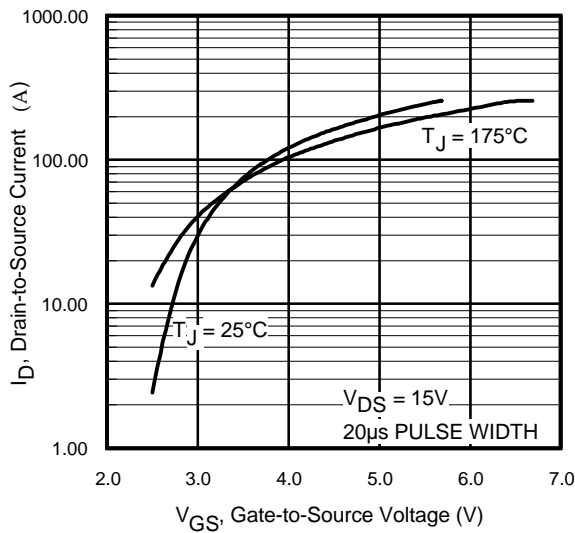


Fig 3. Typical Transfer Characteristics

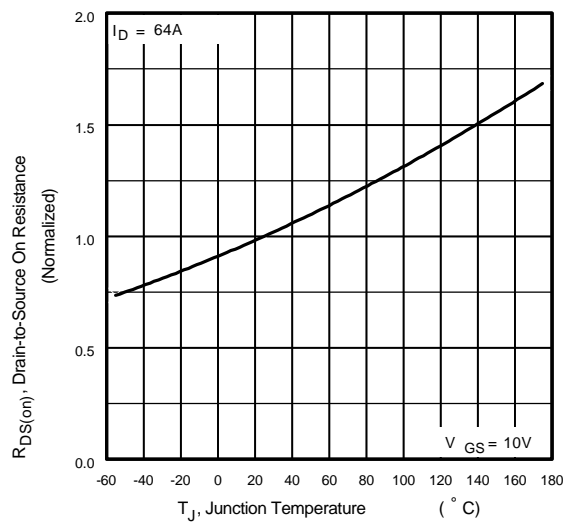


Fig 4. Normalized On-Resistance Vs. Temperature

IRLR7811W

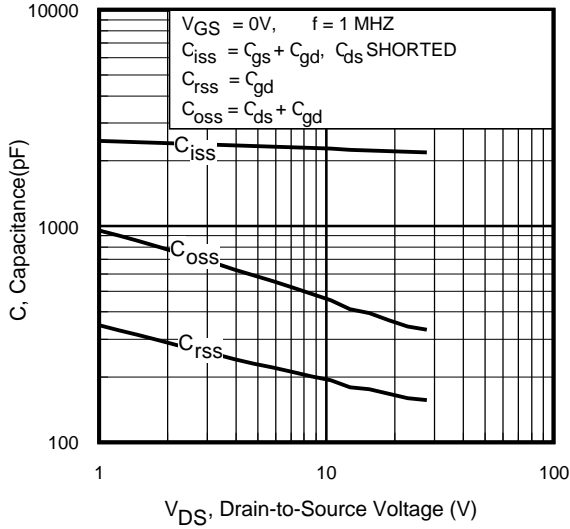


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

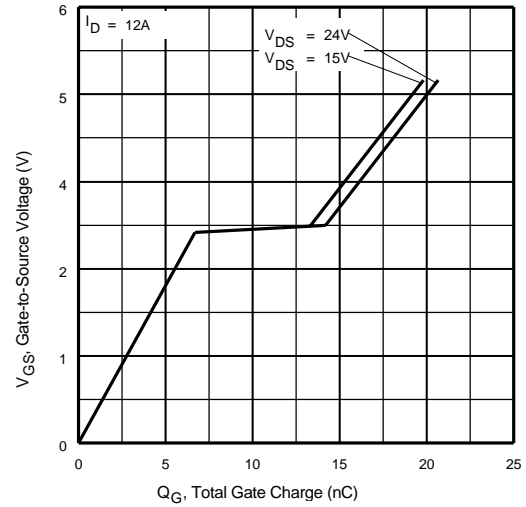


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

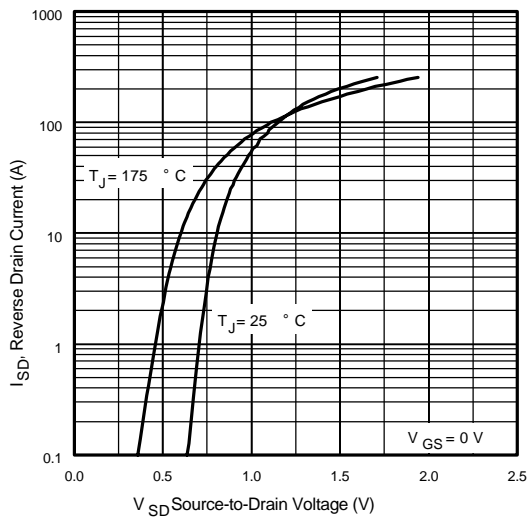


Fig 7. Typical Source-Drain Diode Forward Voltage

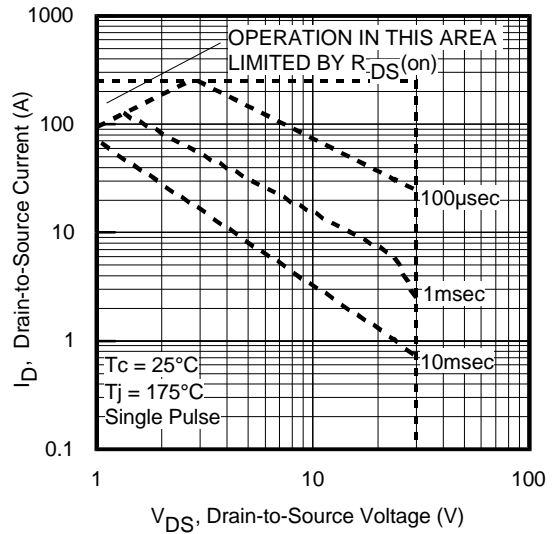


Fig 8. Maximum Safe Operating Area

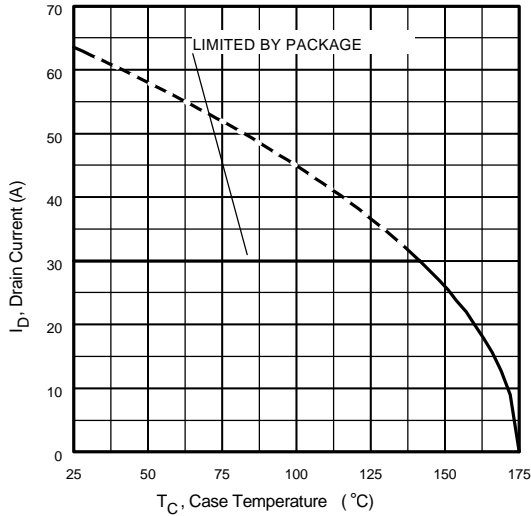


Fig 9. Maximum Drain Current Vs. Case Temperature

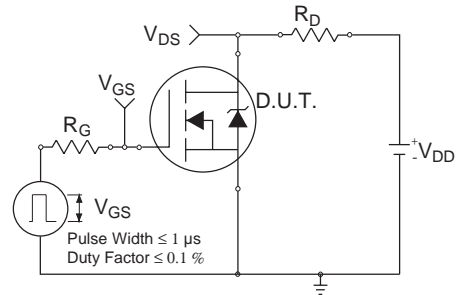


Fig 10a. Switching Time Test Circuit

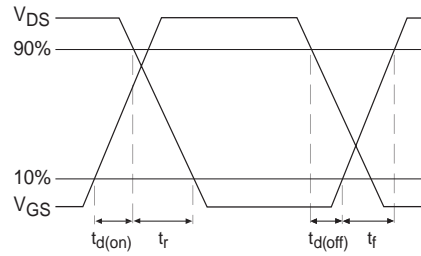


Fig 10b. Switching Time Waveforms

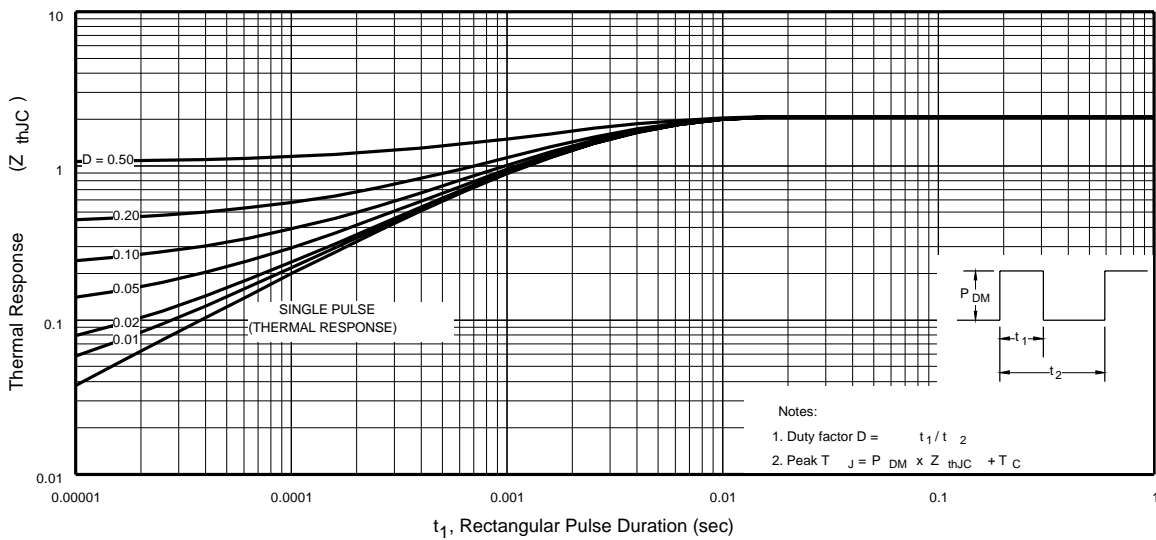


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

IRLR7811W

International
IR Rectifier

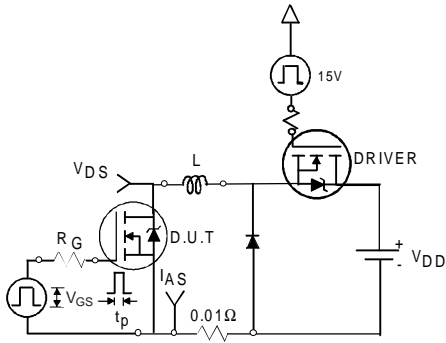


Fig 12a. Unclamped Inductive Test Circuit

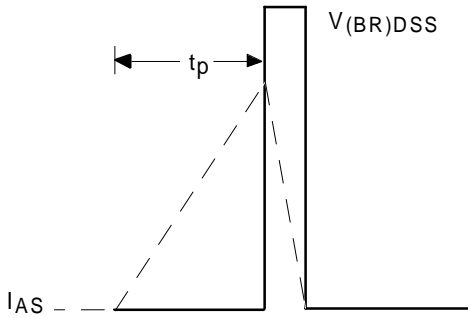


Fig 12b. Unclamped Inductive Waveforms

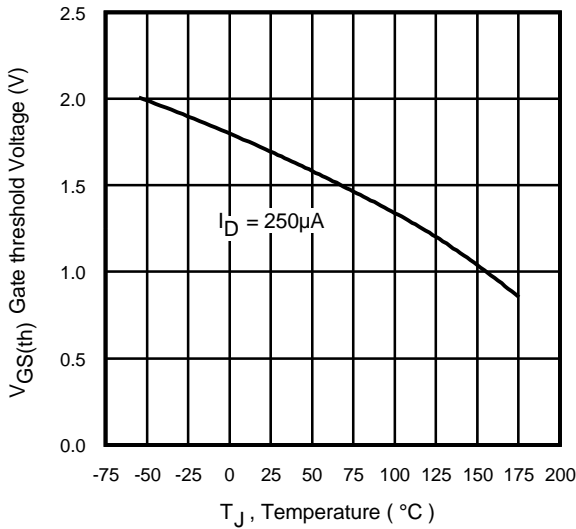


Fig 13. Threshold Voltage Vs. Temperature

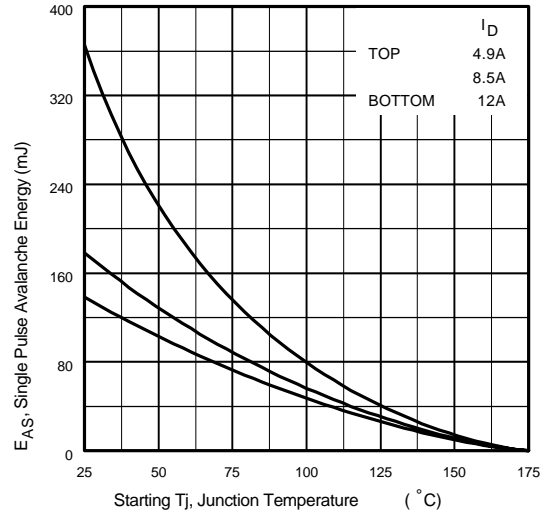


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

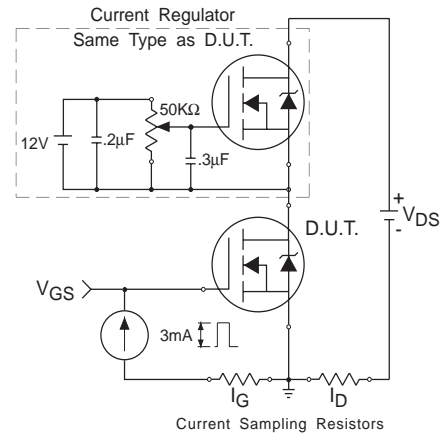


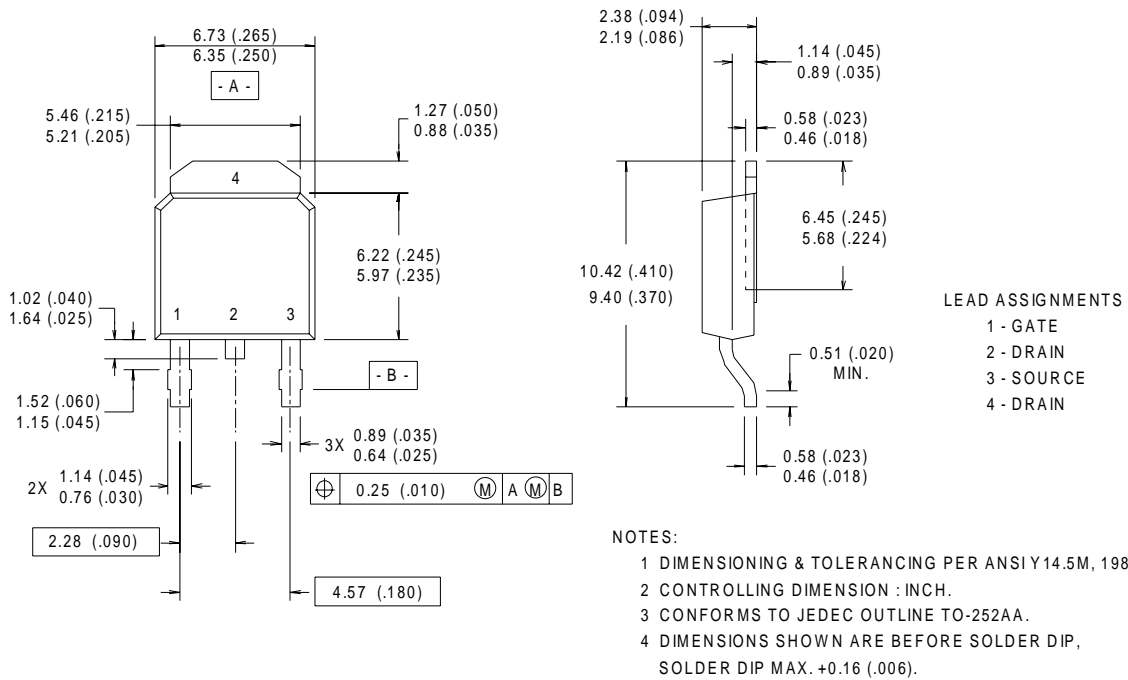
Fig 14. Gate Charge Test Circuit

IRLR7811W



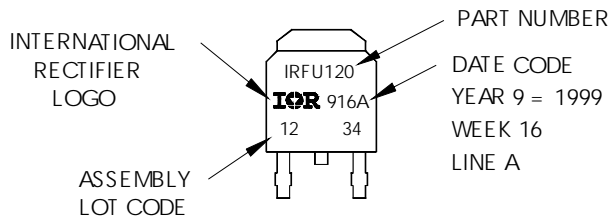
TO-252AA (D-Pak) Package Outline

Dimensions are shown in millimeters (inches)



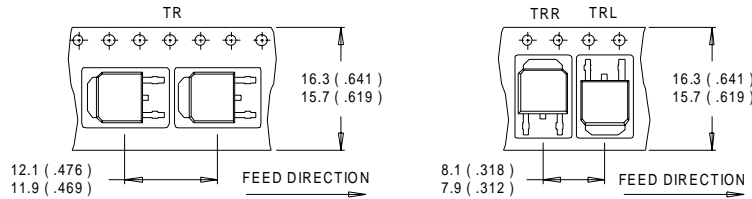
TO-252AA (D-Pak) Part Marking Information

EXAMPLE: THIS IS AN IRFR120
 WITH ASSEMBLY
 LOT CODE 1234
 ASSEMBLED ON WW 16, 1999
 IN THE ASSEMBLY LINE "A"

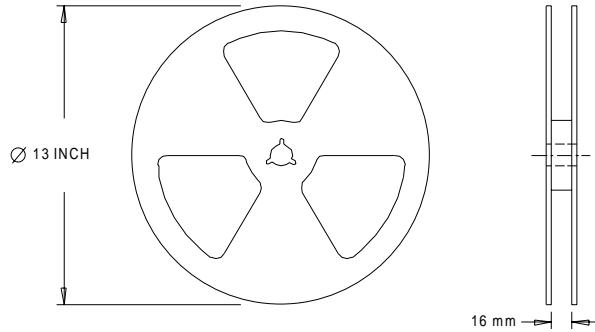


D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. OUTLINE CONFORMS TO EIA-481.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
 - ② Starting $T_J = 25^\circ\text{C}$, $L = 1.9\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = 12\text{A}$.
 - ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
 - ④ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 30A.
- * When mounted on 1" square PCB (FR-4 or G-10 Material).
 For recommended footprint and soldering techniques refer to application note #AN-994.

Data and specifications subject to change without notice.
 This product has been designed and qualified for the Consumer market.
 Qualification Standards can be found on IR's Web site.